Amendments to the CLAIMS:

Without prejudice, this listing of the claims replaces all prior versions and listings of the claims in the present application:

(claims 1-8 canceled)

LISTING OF CLAIMS:

9. (currently amended) A bidirectional semiconductor component, comprising:

a substrate including a drain region; and

two symmetrical MOS transistor structures integrated laterally in the substrate and connected to each other antiserially, a drain terminal of each of the two symmetrical MOS transistor structures being connected to one another, wherein:

a zone having a conductivity that is the same as a conductivity of the drain region and having a doping that is higher than a doping of the drain region is [situated] doped upstream from a pn junction of one of the two symmetrical MOS transistor structures in a junction area with the drain region.

10. (previously presented) The bidirectional semiconductor component according to claim 9, wherein:

the drain region and the zone are n-doped.

11. (previously presented) The bidirectional semiconductor component according to claim 9, further comprising:

a layer on which the drain region is situated and having a doping that is opposite that of the conductivity of the drain region.

12. (currently amended) The bidirectional semiconductor component according to claim 11,wherein:

the layer includes a plurality of partial layers having [stepped] different doping of the same type of conductivity.

13. (currently amended) A method of using a bidirectional semiconductor component, comprising the

step of:

using the bidirectional semiconductor component as a short-circuit switch to short circuit a primary winding of an ignition coil in an ignition power module of an ignition system of an internal combustion engine, wherein the bidirectional semiconductor component includes:

Figs. 1-3

a substrate including a drain region; and

two symmetrical MOS transistor structures integrated laterally in the substrate and connected to each other antiserially, a drain terminal of each of the two symmetrical MOS transistor structures being connected to one another wherein:

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a zone having a conductivity that is the same as a conductivity of the drain region and having a doping that is higher than a doping of the drain region is [situated] doped upstream from a pn junction of one of the two symmetrical MOS transistor structures in a junction area with the drain region.

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14. (currently amended) The method according to claim 13, further comprising the steps of:

performing a time-staggered activation of gate terminals of the two symmetrical MOS transistor structures in a time-staggered manner; and

activating at a later time one of the two symmetrical MOS transistor structures that blocks a higher voltage of one of a battery voltage and a terminal voltage.

15. (previously presented) The method according to claim 14, wherein:

the time-staggered activation is performed by interconnecting a capacitor.

16. (previously presented) The method according to claim 14, wherein:

the time-staggered activation is performed by a time control.